

P-Channel 20V(D-S) MOSFET

Product summary		
V_{DS}	-20	V
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$) Typ.	440	m Ω
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$) Typ.	600	m Ω
I_D ($T_A=25^{\circ}C$)	-0.6	A

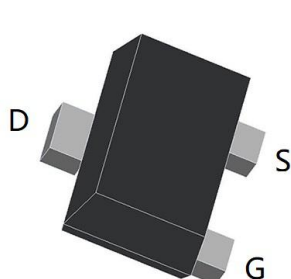
Features

- Low Input Capacitance
- Fast Switching Speed
- Low Gate Threshold Voltage

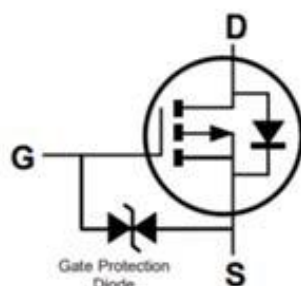
Applications

- Load Switching
- Logic Level Shift

Pin Configuration



SOT-723



Packing Information

Device	Package	Reel Size	Quantity(Min. Package)
ECDK1013E	SOT-723	7"	10000pcs

Absolute Maximum Ratings (at $T_A=25^{\circ}C$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V _{DS}	Drain-Source Voltage		-20	V
V _{GS}	Gate-Source Voltage		±8	V
I _D	Continuous Drain Current at V _{GS} =10V	T _A =25°C	-0.6	A
		T _A =70°C	-0.48	A
I _{DM}	Pulse Drain Current Tested ^A		-1.2	A
P _D	Power Dissipation	T _A =25°C	0.15	W
T _J ,T _{STG}	Junciton and Storage Temperature Range		-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Typical	Units
$R_{\theta JA}$	Thermal Resistance-Junction to ambient ^B	833	$^{\circ}C/W$

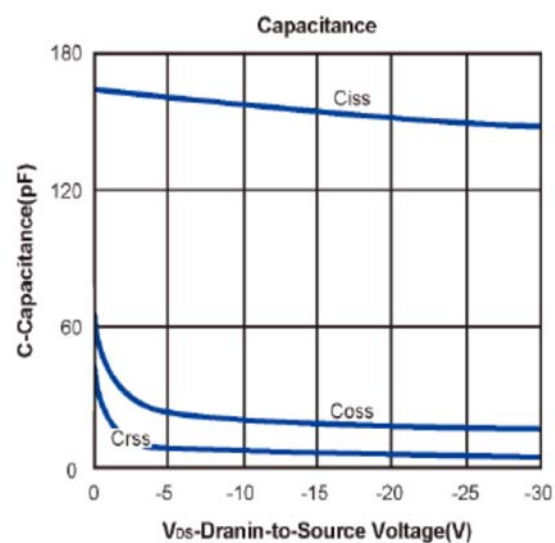
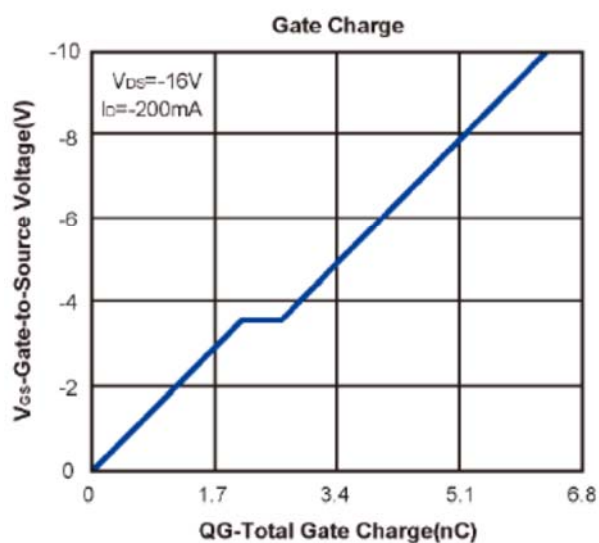
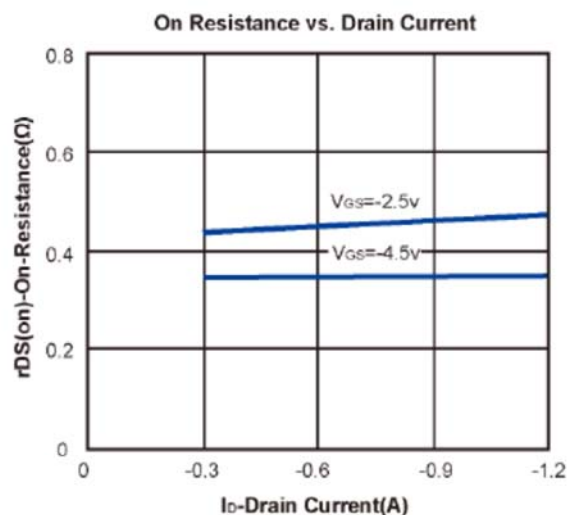
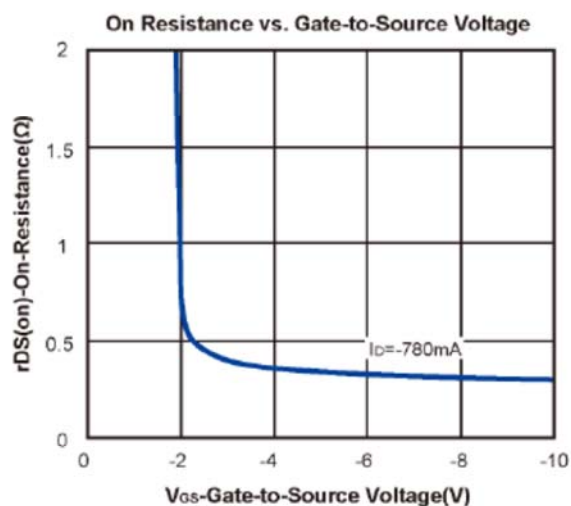
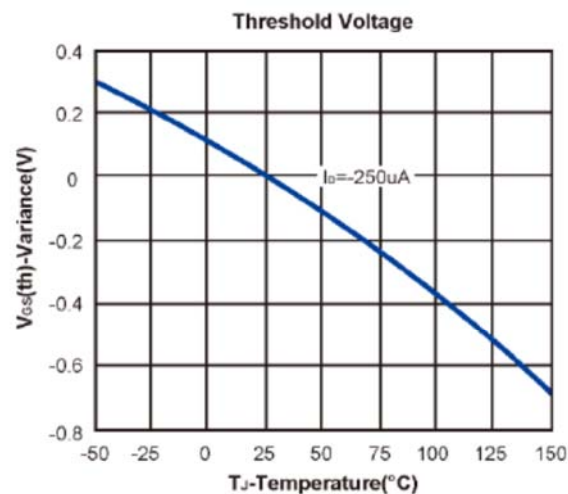
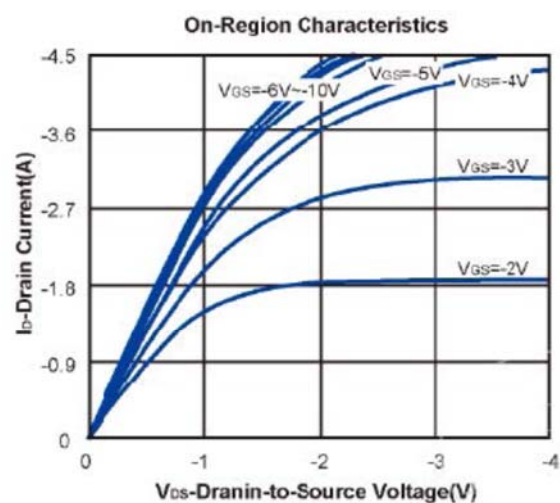
Electrical Characteristics (at $T_J = 25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-20V, V_{GS}=0V$	--	--	-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 8V$	--	--	± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	--	-1.0	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=-4.5V, I_D=-0.7A$	--	440	540	m Ω
		$V_{GS}=-2.5V, I_D=-0.6A$	--	600	720	m Ω
V_{SD}	Forward Voltage	$I_{SD}=-0.35A, V_{GS}=0V$	--	--	-1.2	V
Dynamic and Switching Parameters						
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=-16V$ $f=1\text{MHz}$	--	152	--	pF
C_{oss}	Output Capacitance		--	18	--	pF
C_{rss}	Reverse Transfer Capacitance		--	6	--	pF
Q_g	Total Gate Charge	$V_{DS}=-16V, I_D=-0.2A$ $V_{GS}=-4.5V$	--	2.8	--	nC
Q_{gs}	Gate-Source Charge		--	2.1	--	nC
Q_{gd}	Gate-Drain Charge		--	0.5	--	nC
$t_{D(on)}$	Turn-on Delay Time	$V_{DD}=-10V$ $I_D=-0.2A,$ $R_{GEN}=10\Omega,$ $V_{GS}=-5V$	--	51.3	--	ns
t_r	Turn-on Rise Time		--	24.2	--	ns
$t_{D(off)}$	Turn-off Delay Time		--	246	--	ns
t_f	Turn-off Fall Time		--	81.2	--	ns

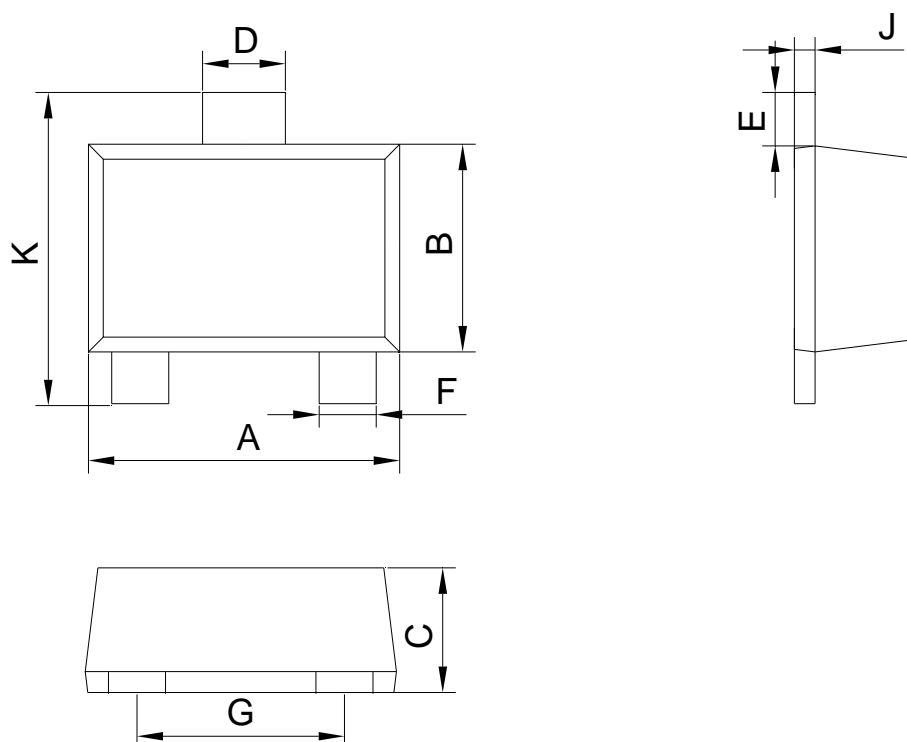
A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 1 inch x 0.062 inch.

Typical Characteristics



SOT-723 Package Information



SOT-723		
Dim	Min	Max
A	1.10	1.30
B	0.70	0.90
C	0.40	0.54
D	0.22	0.42
E	0.10	0.30
F	0.12	0.32
G	0.70	0.90
J	0.08	0.15
K	1.10	1.30